Abstracts

Electromagnetic analysis for microwave FET modeling

E. Larique, S. Mons, D. Baillargeat, S. Verdeyme, M. Aubourg, P. Guillon and R. Quere. "Electromagnetic analysis for microwave FET modeling." 1998 Microwave and Guided Wave Letters 8.1 (Jan. 1998 [MGWL]): 41-43.

This letter presents a technique to analyze complex microwave devices. An electromagnetic three-dimensional (3-D) software is applied to characterize the distributed part of the structure. It is coupled to a circuit simulator to introduce the contribution on the electrical response of the localized passive or active elements contained in the device. The link between the two parts is made thanks to a new type of access, "the localized access". We have applied this method to the study of a field effect transistor and good agreements are observed between simulations and measurements from 1 to 30 GHz.

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